Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	(((solid adj state) semiconductor metal gate) near (layer film material)) AND (((no near more) less) near "40" near Angstroms) AND (atomic$4 near smooth near surface) AND ((metallurgical$3 metal$3) near bond$3) AND (sufficient$2 uniform$2 (defect near free$2)).CLM.	US-PGPUB; USPAT	OR	ON	2005/11/04 08:24
L2	1	(method process$3 fabricat$3) AND (((solid adj state) semiconductor metal gate) near (layer film material)) AND (((no near more) less) near "40" near Angstroms) AND (atomic$4 near smooth near surface) AND ((metallurgical$3 metal$3) near bond$3) AND (sufficient$2 uniform$2 (defect near free$2)).CLM.	US-PGPUB; USPAT	OR	ON	2005/11/04 08:26
L3	1	(method process$3 fabricat$3) AND (((solid adj state) semiconductor metal gate) near (layer film material)) AND pocket AND (((no near more) less) near "40" near Angstroms) AND (atomic$4 near smooth near surface) AND ((metallurgical$3 metal$3) near bond$3) AND (sufficient$2 uniform$2 (defect near free$2)).CLM.	US-PGPUB; USPAT	OR	ON	2005/11/04 08:29
L4	0	(method process$3 fabricat$3) AND (((solid adj state) semiconductor metal gate) near (layer film material)) AND pocket AND (((no near more) less) near "40" near Angstroms) AND (atomic$4 near smooth near surface) AND ((metallurgical$3 metal$3) near bond$3) AND (sufficient$2 uniform$2 (defect near free$2)) AND signal AND (interfac$3 near rectify$3 near barrier).CLM.	US-PGPUB; USPAT	OR	ON	2005/11/04 08:28
L5	1	(method process$3 fabricat$3) AND (((solid adj state) semiconductor metal gate) near (layer film material)) AND pocket AND (((no near more) less) near (("0.1" near micron) ("40" near Angstroms))) AND (atomic$4 near smooth near surface) AND ((metallurgical$3 metal$3) near bond$3) AND (sufficient$2 uniform$2 (defect near free$2)).CLM.	US-PGPUB; USPAT	OR	ON	2005/11/04 08:36
L6	2524	438/22,24,27,142,421.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/04 08:41
L7	1791	257/9,140,146,496,510.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/04 08:42

L8	2524	5 or 6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/04 08:42
L9	4295	6 or 7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/04 08:42
L10	2751	9 and ((solid adj state) semiconductor metal gate field) near (layer film material)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/04 08:43
L11	92	10 and ((metal$3 metallurgical$2) near bond$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/04 09:03
L12	110	9 and ((metal$3 metallurgical$2) near bond$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/04 09:04